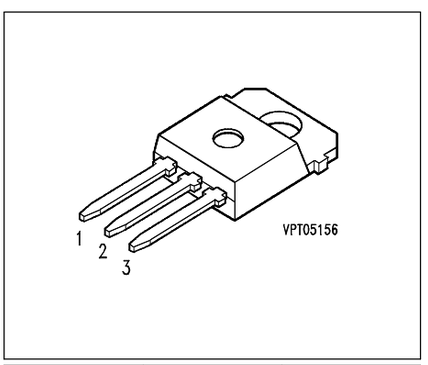
TAVAKOL ELECTRONIC
توکل الکترونیک
مرجع تخصصی تأمین قطعات الکترونیکی اورجینال
این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وب‌سایت توکل الکترونیک مراجعه فرمایید.
مشاهده قیمت و خرید
برای خرید و مشاهده سایر محصولات کلیک کنید

SIEMENS **BUZ 385**

SIPMOS ® Power Transistor

- N channel
- Enhancement mode
- FREDFET



Pin 1	Pin 2	Pin 3
G	D	S

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Ordering Code
BUZ 385	500 V	9 A	0.8 Ω	TO-218 AA	C67078-A3210-A2

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain source voltage	V_{DS}	500	V
Drain-gate voltage R_{GS} = 20 kΩ	V_{DGR}	500	
Continuous drain current T_C = 25 °C	I_D	9	A
Pulsed drain current T_C = 25 °C	I_{Dpuls}	36	
Gate source voltage	V_{GS}	± 20	V
Power dissipation T_C = 25 °C	P_{tot}	125	W
Operating temperature	T_j	-55 ... + 150	°C
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip case	R_{thJC}	≤ 1	K/W
Thermal resistance, chip to ambient	R_{thJA}	75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage V_{GS} = 0 V, I_D = 0.25 mA, T_j = 25 °C	$V_{(BR)DSS}$	500	-	-	V
Gate threshold voltage V_{GS}=V_{DS}, I_D = 1 mA	$V_{GS(th)}$	2.1	3.5	4	
Zero gate voltage drain current V_{DS} = 500 V, V_{GS} = 0 V, T_j = 25 °C V_{DS} = 500 V, V_{GS} = 0 V, T_j = 125 °C	I_{DSS}	- -	20 100	250 1000	µA
Gate-source leakage current V_{GS} = 20 V, V_{DS} = 0 V	I_{GSS}	-	10	100	nA
Drain-Source on-resistance V_{GS} = 10 V, I_D = 6.5 A	$R_{DS(on)}$	-	0.6	0.8	Ω

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

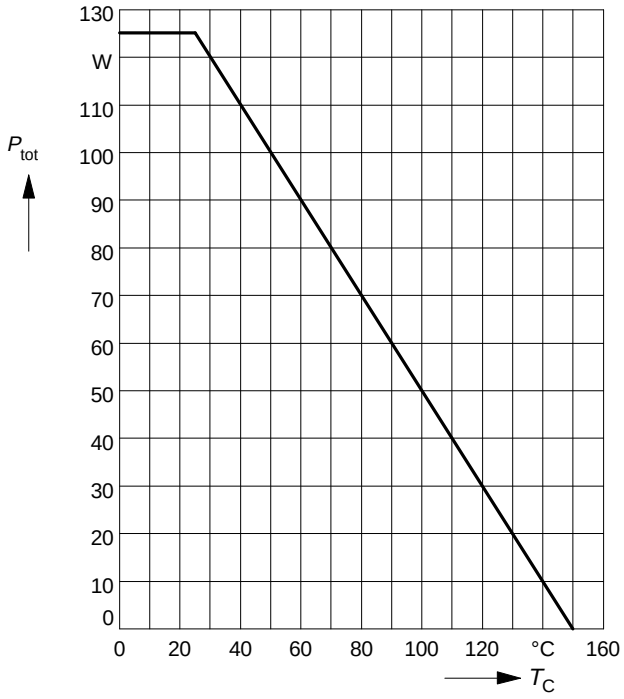
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, I_D = 6.5 A	g_{fs}	2.7	6.7	-	S
Input capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{iss}	-	3800	4900	pF
Output capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{oss}	-	250	400	
Reverse transfer capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{rss}	-	100	170	
Turn-on delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.8 A R_{GS} = 50 Ω	$t_{d(on)}$	-	50	75	ns
Rise time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.8 A R_{GS} = 50 Ω	t_r	-	80	120	
Turn-off delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.8 A R_{GS} = 50 Ω	$t_{d(off)}$	-	330	430	
Fall time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.8 A R_{GS} = 50 Ω	t_f	-	110	140	

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current T_C = 25 °C	I_S	-	-	9	A
Inverse diode direct current,pulsed T_C = 25 °C	I_{SM}	-	-	36	
Inverse diode forward voltage V_{GS} = 0 V, I_F = 21 A	V_{SD}	-	1.3	1.7	V
Reverse recovery time V_R = 100 V, I_F=I_S, di_F/dt = 100 A/µs	t_{rr}	-	180	250	ns
Reverse recovery charge V_R = 100 V, I_F=I_S, di_F/dt = 100 A/µs	Q_{rr}	-	0.65	1.2	µC

Power dissipation

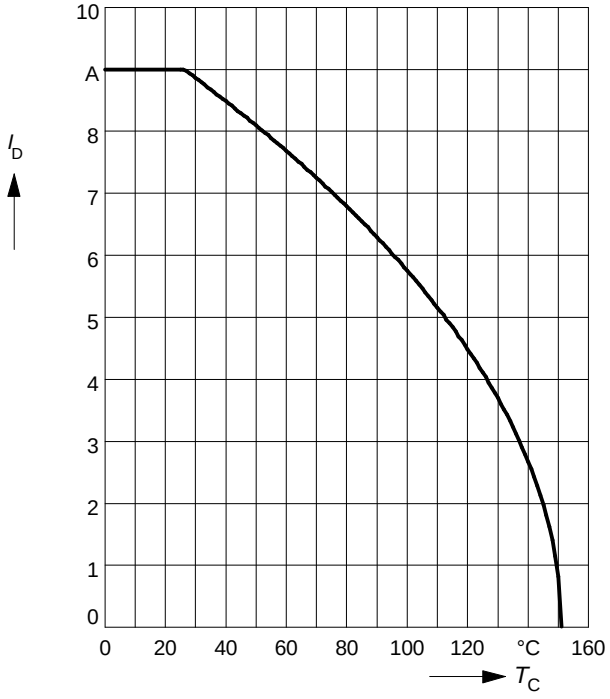
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

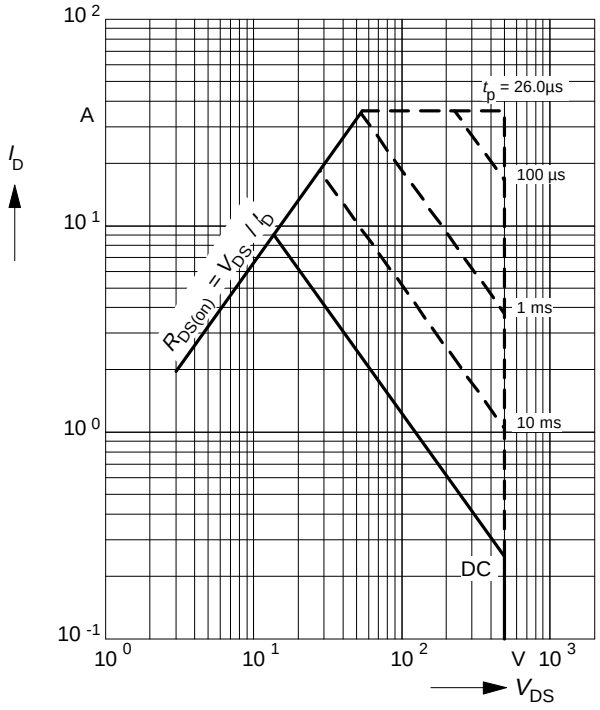
parameter: $V_{GS} \geq 10$ V



Safe operating area

$I_D = f(V_{DS})$

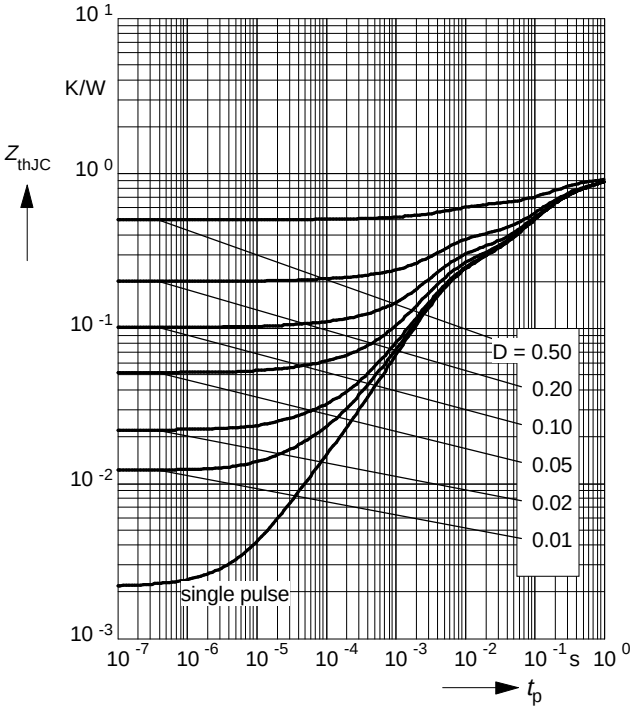
parameter: $D = 0.01$, $T_C = 25$°C



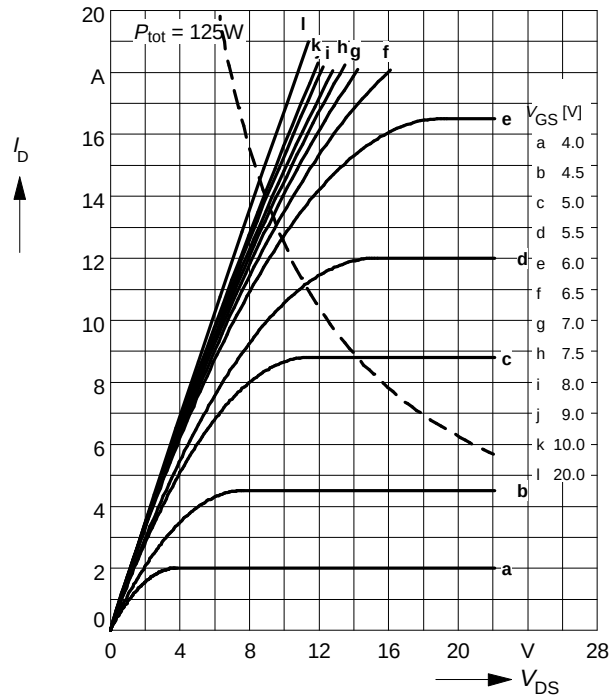
Transient thermal impedance

$Z_{th\,JC} = f(t_p)$

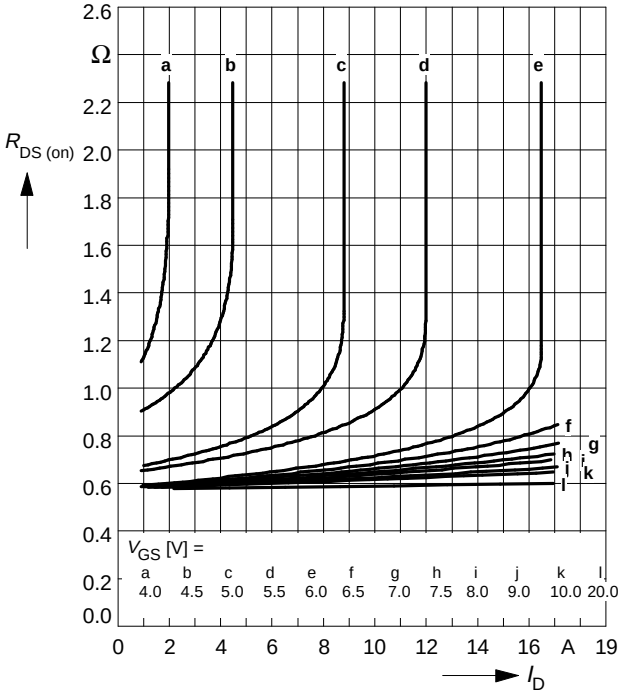
parameter: $D = t_p / T$



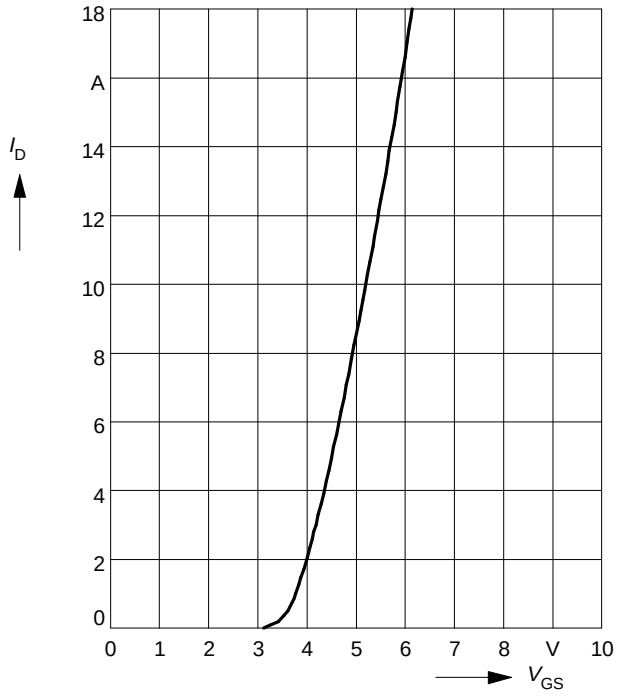
Typ. output characteristics
$I_D = f(V_{DS})$
parameter: t_p = 80 µs



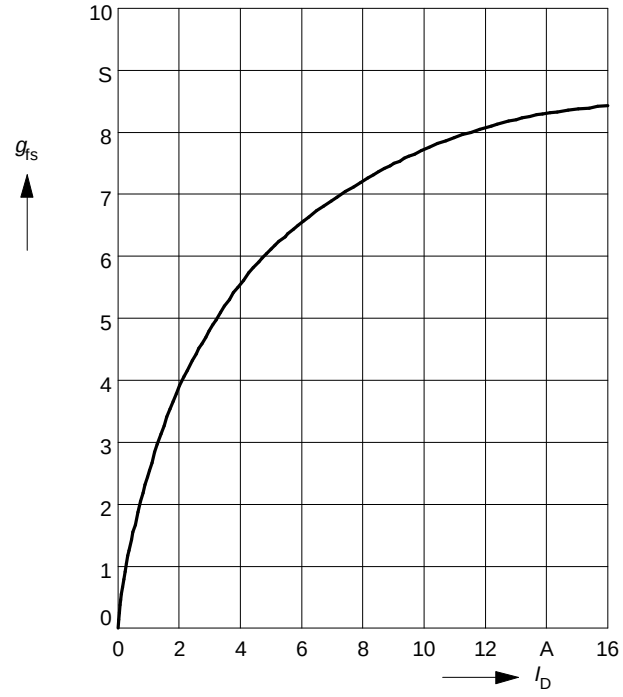
Typ. drain-source on-resistance
$R_{DS\ (on)} = f(I_D)$
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$
parameter: t_p = 80 µs
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

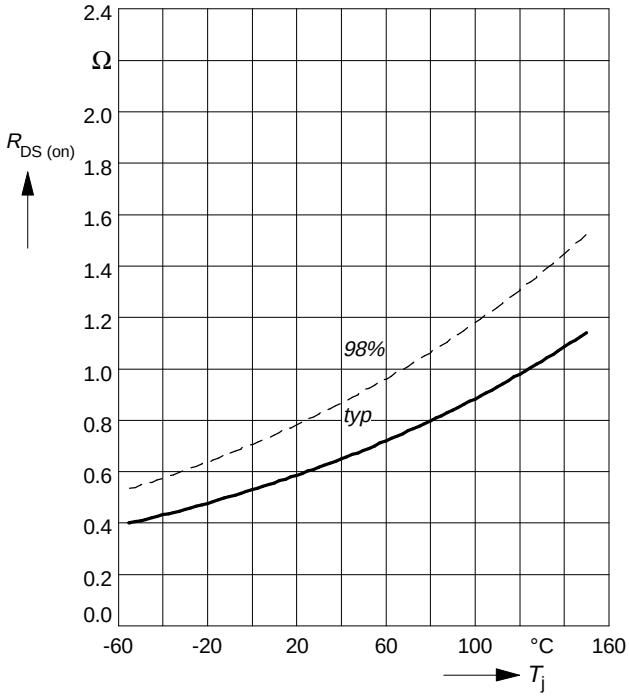


Typ. forward transconductance $g_{fs} = f(I_D)$
parameter: t_p = 80 µs,
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



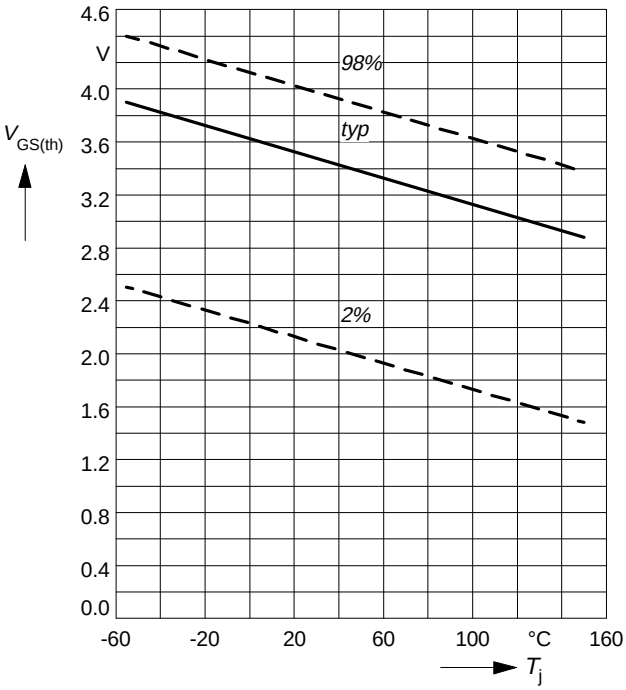
Drain-source on-resistance

$R_{DS\ (on)} = f(T_j)$
parameter: I_D = 6.5 A, V_{GS} = 10 V



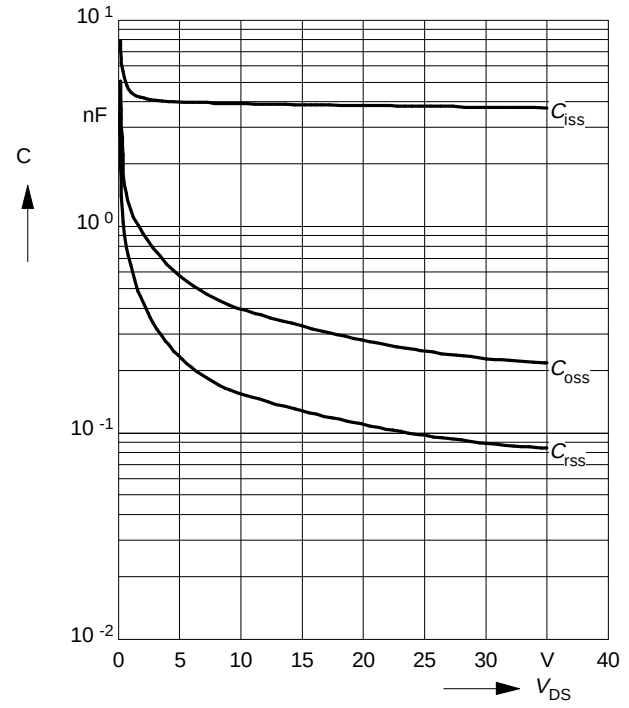
Gate threshold voltage

$V_{GS\ (th)} = f(T_j)$
parameter: $V_{GS} = V_{DS}$, I_D = 1 mA



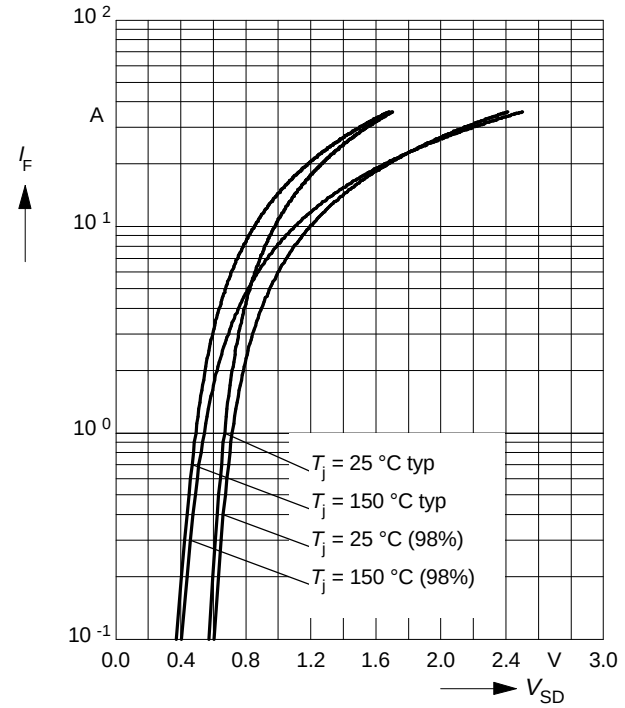
Typ. capacitances

$C = f(V_{DS})$
parameter: V_{GS} = 0V, f = 1MHz



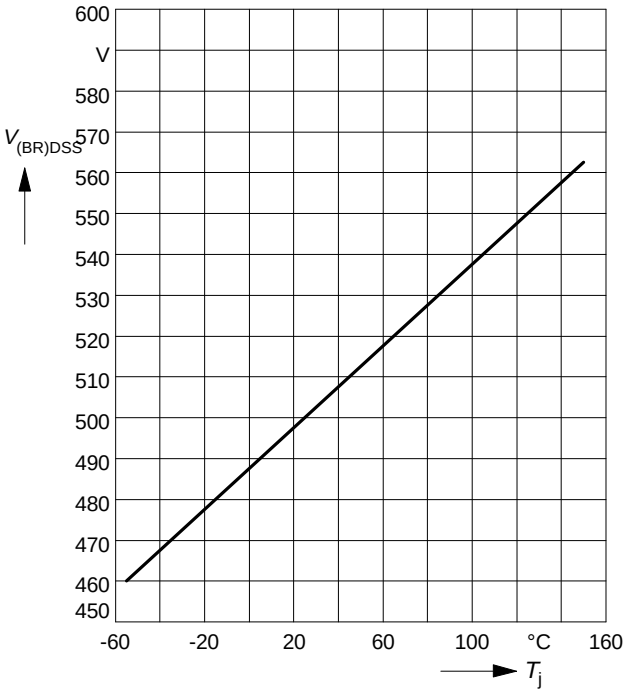
Forward characteristics of reverse diode

$I_F = f(V_{SD})$
parameter: T_j, t_p = 80 µs



Drain-source breakdown voltage

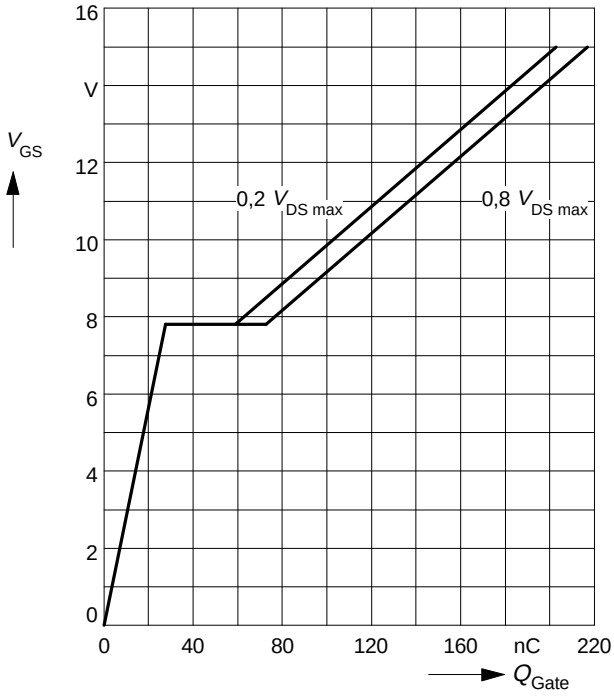
$V_{(BR)DSS} = f(T_j)$



Typ. gate charge

$V_{GS} = f(Q_{Gate})$

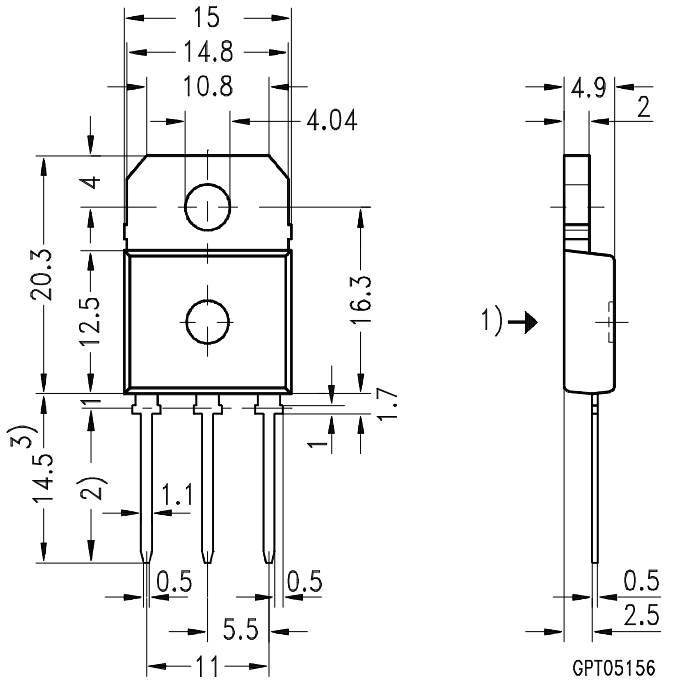
parameter: $I_{D\ puls}$ = 14 A



Package Outlines

TO-218 AA

Dimension in mm



1) punch direction, burr max. 0.04
2) dip tinning
3) max. 15.5 by dip tinning press burr max. 0.05